

 $I_D$ 

# PHD101NQ03LT

N-channel TrenchMOS logic level FET Rev. 5 — 31 October 2011

Product data sheet

#### **Product profile** 1.

#### 1.1 General description

Logic level N-channel enhancement mode Field-Effect Transistor (FET) in a plastic package using TrenchMOS technology. This product is designed and qualified for use in computing, communications, consumer and industrial applications only.

### 1.2 Features and benefits

- Low conduction losses due to low on-state resistance
- Simple gate drive required due to low gate charge

### 1.3 Applications

DC-to-DC converters

### 1.4 Quick reference data

Table 1. **Quick reference data** Symbol Parameter Conditions Min Тур Max Unit drain-source voltage T<sub>i</sub> ≥ 25 °C; T<sub>i</sub> ≤ 175 °C 30 ۷ VDS - $T_{mb} = 25 \text{ °C}; V_{GS} = 10 \text{ V}; \text{ see Figure 1};$ drain current \_ 75 А \_ see Figure 3 P<sub>tot</sub> total power dissipation T<sub>mb</sub> = 25 °C; see Figure 2 166 W --Static characteristics drain-source on-state  $V_{GS} = 10 \text{ V}; I_D = 25 \text{ A}; T_i = 25 \text{ °C};$ 4.5 5.5 mΩ **R**<sub>DSon</sub> \_ resistance see Figure 9; see Figure 10 **Dynamic characteristics** nC  $Q_{GD}$ gate-drain charge  $V_{GS} = 5 \text{ V}; I_D = 50 \text{ A}; V_{DS} = 15 \text{ V};$ 8 T<sub>i</sub> = 25 °C; see Figure 11

Suitable for logic level gate drive sources



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## 2. Pinning information

Table 2.	Pinning	information			
Pin	Symbol	Description	Simplified outline	Graphic symbol	
1	G	gate		_	
2	D	drain <sup>[1]</sup>	mb		
3	S	source			
mb	D mounting base; connected to dra	mounting base; connected to drain		mbbo76 S	
			SOT428 (DPAK)		

[1] It is not possible to make a connection to pin 2.

## 3. Ordering information

#### Table 3. Ordering information

Type number	Package			
	Name	Description	Version	
PHD101NQ03LT	DPAK	plastic single-ended surface-mounted package (DPAK); 3 leads (one lead cropped)	SOT428	

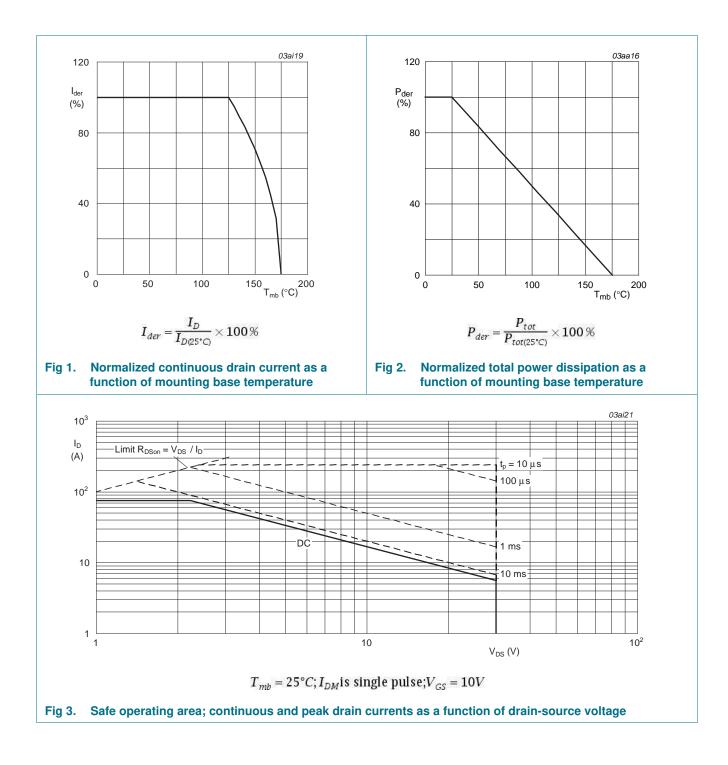
## 4. Limiting values

#### Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Мах	Unit
V <sub>DS</sub>	drain-source voltage	T <sub>j</sub> ≥ 25 °C; T <sub>j</sub> ≤ 175 °C	-	30	V
V <sub>DGR</sub>	drain-gate voltage	$T_j \ge 25 \text{ °C}; T_j \le 175 \text{ °C}; R_{GS} = 20 \text{ k}\Omega$	-	30	V
V <sub>GS</sub>	gate-source voltage		-20	20	V
I <sub>D</sub>	drain current	$V_{GS}$ = 10 V; $T_{mb}$ = 100 °C; see <u>Figure 1</u>	-	75	А
		$V_{GS}$ = 10 V; $T_{mb}$ = 25 °C; see <u>Figure 1</u> ; see <u>Figure 3</u>	-	75	A
I <sub>DM</sub>	peak drain current	pulsed; $t_p \le 10 \ \mu s$ ; $T_{mb} = 25 \ ^{\circ}C$ ; see Figure 3	-	240	А
P <sub>tot</sub>	total power dissipation	T <sub>mb</sub> = 25 °C; see <u>Figure 2</u>	-	166	W
T <sub>stg</sub>	storage temperature		-55	175	°C
Tj	junction temperature		-55	175	°C
V <sub>GSM</sub>	peak gate-source voltage	pulsed; $\delta = 25$ %; $t_p \le 50 \ \mu s$	-25	25	V
Source-drai	n diode				
I <sub>S</sub>	source current	T <sub>mb</sub> = 25 °C	-	75	А
I <sub>SM</sub>	peak source current	pulsed; $t_p \le 10 \ \mu s$ ; $T_{mb} = 25 \ ^{\circ}C$	-	240	А
Avalanche r	ruggedness				
$E_{DS(AL)S}$	non-repetitive drain-source avalanche energy	$ \begin{array}{l} V_{GS} = 10 \; V; \; T_{j(init)} = 25 \; ^{\circ}C; \; I_{D} = 43 \; A; \\ V_{sup} \leq 15 \; V; \; unclamped; \; t_{p} = 0.19 \; ms; \\ R_{GS} = 50 \; \Omega \end{array} $	-	185	mJ
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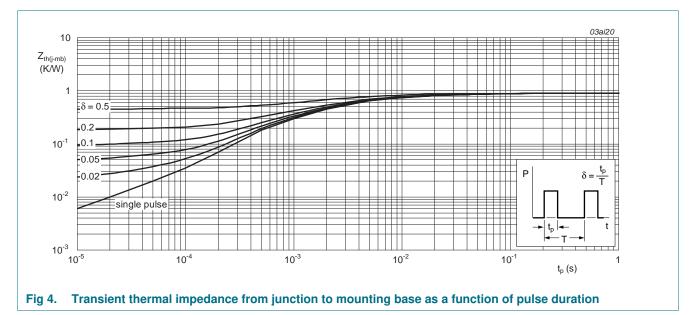


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## 5. Thermal characteristics

Table 5.	Thermal characteristics						
Symbol	Parameter	Conditions		Min	Тур	Max	Unit
$R_{th(j-mb)}$	thermal resistance from junction to mounting base	see <u>Figure 4</u>		-	-	0.9	K/W
R <sub>th(j-a)</sub>	thermal resistance from junction to ambient	minimum footprint	[1]	-	75	-	K/W
		SOT404 minimum footprint	[1]	-	50	-	K/W

[1] Mounted on a printed-circuit board; vertical in still air.



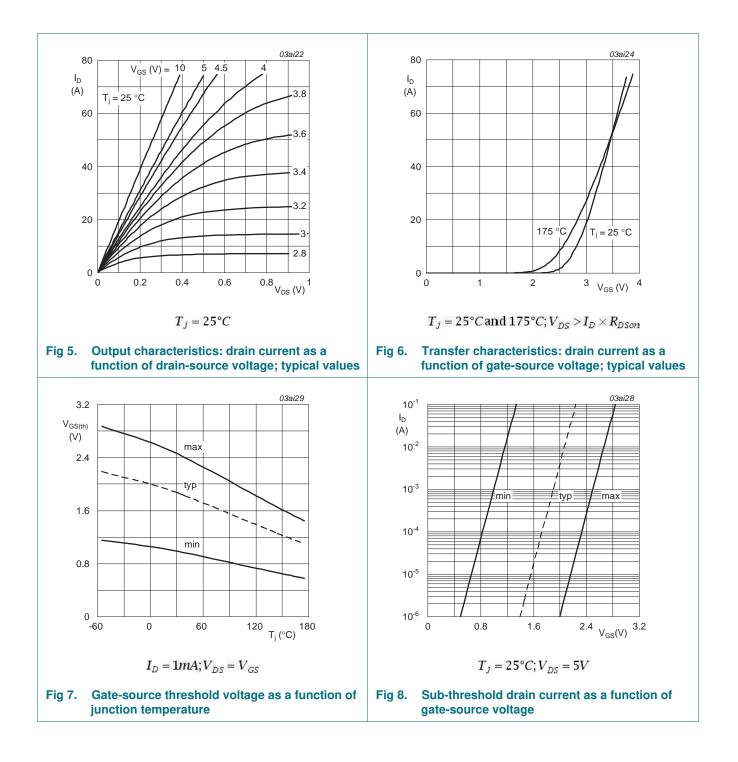
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## 6. Characteristics

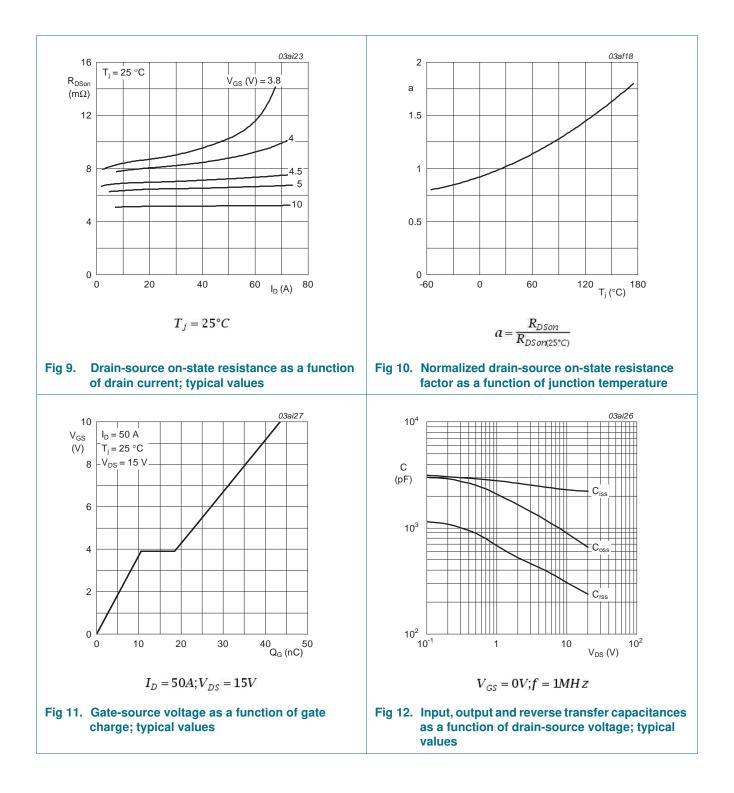
Table 6.	Characteristics					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static cha	aracteristics					
V <sub>(BR)DSS</sub>	drain-source breakdown voltage	$I_D = 250 \ \mu A; \ V_{GS} = 0 \ V; \ T_j = -55 \ ^\circ C$	27	-	-	V
		$I_D = 250 \ \mu\text{A}; \ V_{GS} = 0 \ V; \ T_j = 25 \ ^\circ\text{C}$	30	-	-	V
V <sub>GS(th)</sub>	gate-source threshold voltage	I <sub>D</sub> = 1 mA; V <sub>DS</sub> = V <sub>GS</sub> ; T <sub>j</sub> = 175 °C; see <u>Figure 7</u> ; see <u>Figure 8</u>	0.6	-	-	V
		$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = -55 \text{ °C};$ see <u>Figure 7</u> ; see <u>Figure 8</u>	-	-	2.9	V
		I <sub>D</sub> = 1 mA; V <sub>DS</sub> = V <sub>GS</sub> ; T <sub>j</sub> = 25 °C; see <u>Figure 7</u> ; see <u>Figure 8</u>	1	1.9	2.5	V
I <sub>DSS</sub>	drain leakage current	$V_{DS} = 30 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	0.05	1	μA
		$V_{DS} = 30 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 175 \text{ °C}$	-	-	500	μA
I <sub>GSS</sub>	gate leakage current	$V_{GS} = 20 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	10	100	nA
		$V_{GS}$ = -20 V; $V_{DS}$ = 0 V; $T_j$ = 25 °C	-	10	100	nA
R <sub>DSon</sub>	drain-source on-state resistance	$V_{GS}$ = 10 V; $I_D$ = 25 A; $T_j$ = 25 °C; see <u>Figure 9</u> ; see <u>Figure 10</u>	-	4.5	5.5	mΩ
		$V_{GS} = 5 \text{ V}; I_D = 25 \text{ A}; T_j = 175 \text{ °C};$ see <u>Figure 9</u> ; see <u>Figure 10</u>	-	10.5	13.5	mΩ
		V <sub>GS</sub> = 5 V; I <sub>D</sub> = 25 A; T <sub>j</sub> = 25 °C; see <u>Figure 9</u> ; see <u>Figure 10</u>	-	5.8	7.5	mΩ
Dynamic	characteristics					
Q <sub>G(tot)</sub>	total gate charge	$I_D = 50 \text{ A}; V_{DS} = 15 \text{ V}; V_{GS} = 5 \text{ V};$	-	23	-	nC
Q <sub>GS</sub>	gate-source charge	$T_j = 25 \text{ °C}; \text{ see } \frac{\text{Figure } 11}{1}$	-	10.5	-	nC
Q <sub>GD</sub>	gate-drain charge		-	8	-	nC
C <sub>iss</sub>	input capacitance	$V_{DS} = 25 V; V_{GS} = 0 V; f = 1 MHz;$	-	2180	-	pF
C <sub>oss</sub>	output capacitance	$T_j = 25 \text{ °C}; \text{ see } \frac{\text{Figure } 12}{12}$	-	600	-	pF
C <sub>rss</sub>	reverse transfer capacitance		-	225	-	pF
t <sub>d(on)</sub>	turn-on delay time	$V_{DS} = 15 \; V; \; R_L = 0.6 \; \Omega; \; V_{GS} = 4.5 \; V; \;$	-	23	-	ns
t <sub>r</sub>	rise time	$R_{G(ext)} = 5.6 \ \Omega; \ T_j = 25 \ ^{\circ}C; \ I_D = 25 \ A$	-	90	-	ns
t <sub>d(off)</sub>	turn-off delay time		-	37	-	ns
t <sub>f</sub>	fall time		-	33	-	ns
Source-d	rain diode					
V <sub>SD</sub>	source-drain voltage	I <sub>S</sub> = 25 A; V <sub>GS</sub> = 0 V; T <sub>j</sub> = 25 °C; see <u>Figure 13</u>	-	0.85	1.2	V
t <sub>rr</sub>	reverse recovery time	$I_{S} = 10 \text{ A}; \text{ d}I_{S}/\text{d}t = -100 \text{ A}/\mu\text{s};$	-	37	-	ns
Q <sub>r</sub>	recovered charge	$V_{GS} = 0 \text{ V}; V_{DS} = 25 \text{ V}; T_j = 25 \text{ °C}$	-	33	-	nC

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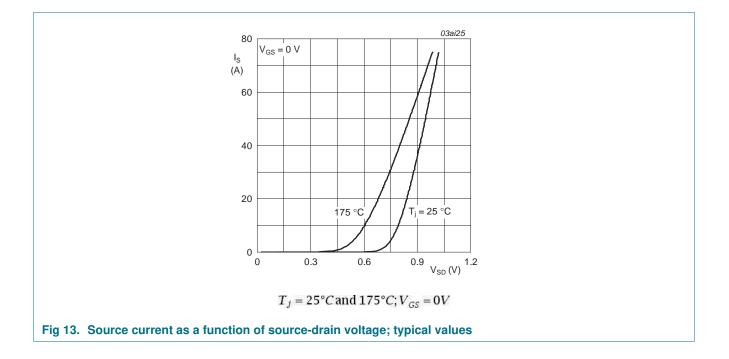
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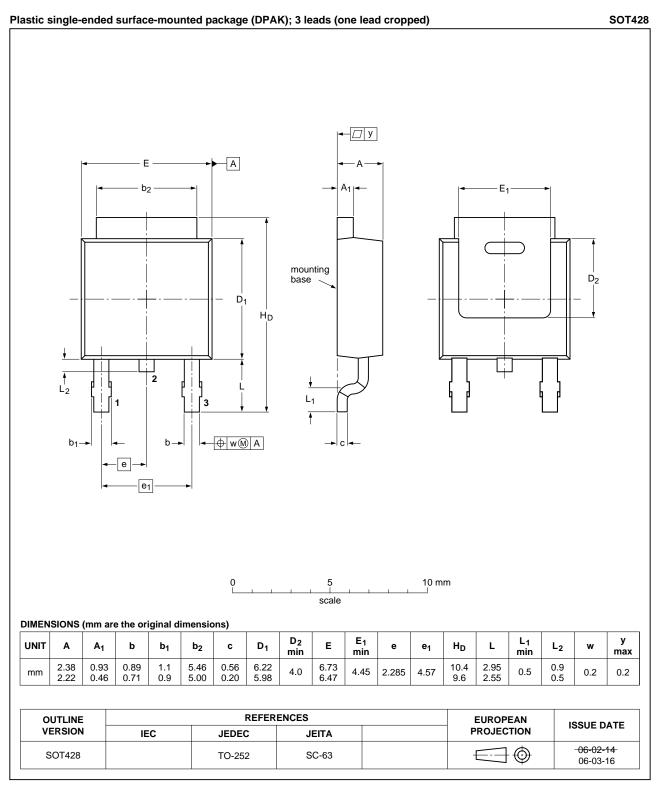


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## 7. Package outline



#### Fig 14. Package outline SOT428 (DPAK)

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### N-channel TrenchMOS logic level FET

## 8. Revision history

Table 7.Revision h	nistory			
Document ID	Release date	Data sheet status	Change notice	Supersedes
PHD101NQ03LT v.5	20111031	Product data sheet	-	PHD101NQ03LT v.4
Modifications:	<ul> <li>Various changes</li> </ul>	to content.		
PHD101NQ03LT v.4	20090609	Product data sheet	-	PHD101NQ03LT v.3

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## 9. Legal information

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Document status [1] [2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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